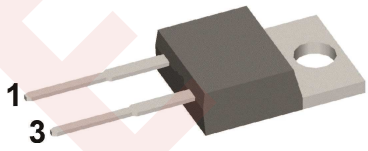
FRED

V_{RRM} = 1000 V
I_{FAV} = 12 A
t_{rr} = 45 ns

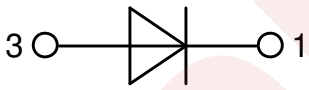
Fast Recovery Epitaxial Diode
Single Diode

Part number

DSEI12-10A



Backside: cathode



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Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

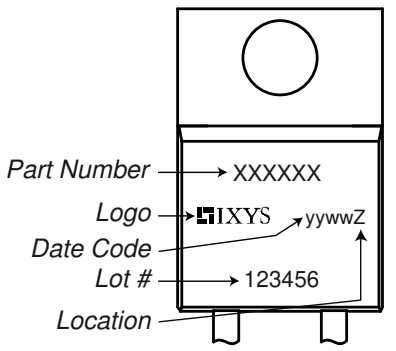
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1000	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1000	V
I_R	*reverse current, drain current*	V_R = 1000 V	T_{VJ} = 25°C			250	µA
		V_R = 800 V	T_{VJ} = 125°C			4	mA
V_F	*forward voltage drop*	I_F = 12 A	T_{VJ} = 25°C			2.68	V
		I_F = 24 A				3.02	V
		I_F = 12 A	T_{VJ} = 150°C			2.12	V
		I_F = 24 A				2.57	V
I_{FAV}	*average forward current*	T_C = 100°C	T_{VJ} = 150°C			12	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			1.72	V
r_F	*slope resistance* }					34	mΩ
R_{thJC}	*thermal resistance junction to case*					1.6	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.50		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			78	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			75	A
C_J	*junction capacitance*	V_R = 500 V f = 1 MHz	T_{VJ} = 25°C		8		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25 °C		4		A
		I_F = 12 A; V_R = 540 V	T_{VJ} = 100 °C		7		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 100 A/µs	T_{VJ} = 25 °C		90		ns
			T_{VJ} = 100 °C		150		ns

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Package TO-220			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			25	A
T_{VJ}	*virtual junction temperature*		-40		150	°C
T_{op}	*operation temperature*		-40		125	°C
T_{stg}	*storage temperature*		-40		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N

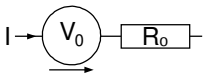
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI12-10A	DSEI12-10A	Tube	50	434434

Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 150°C$

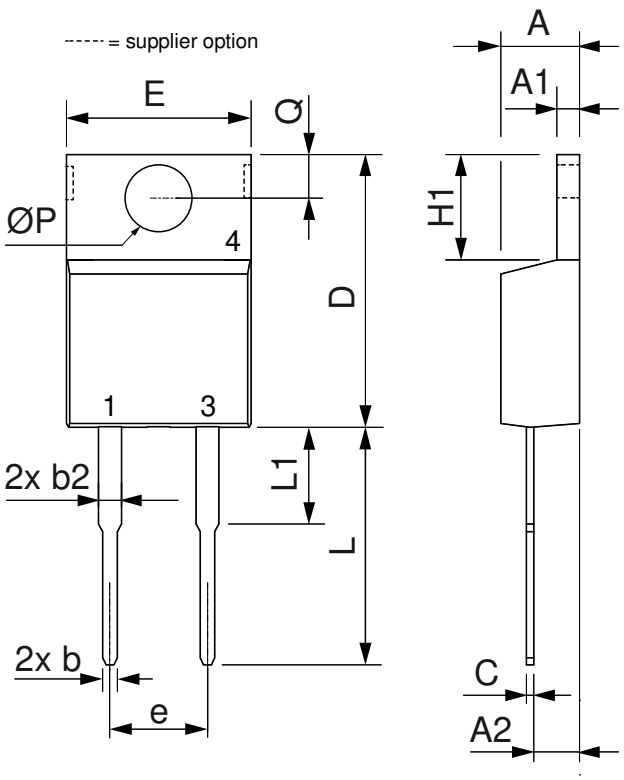


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	1.72	V
$R_{0\,max}$	*slope resistance **	31	mΩ

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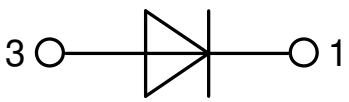
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Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125

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Fast Diode

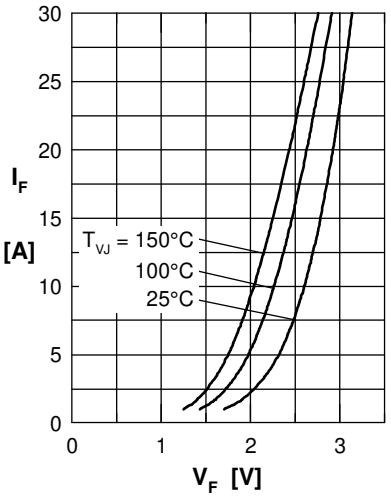


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

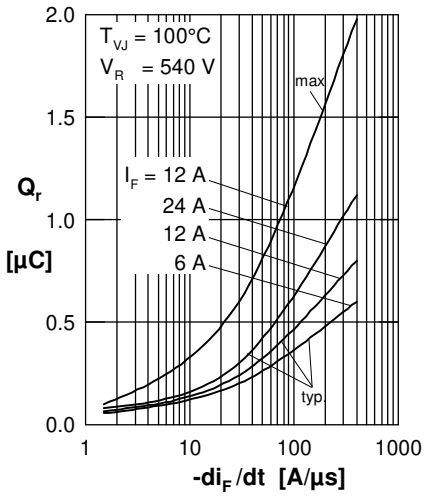


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

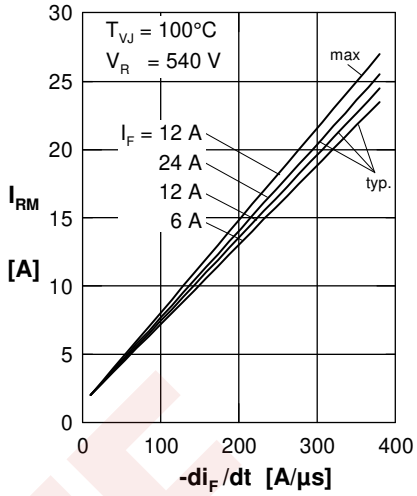


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

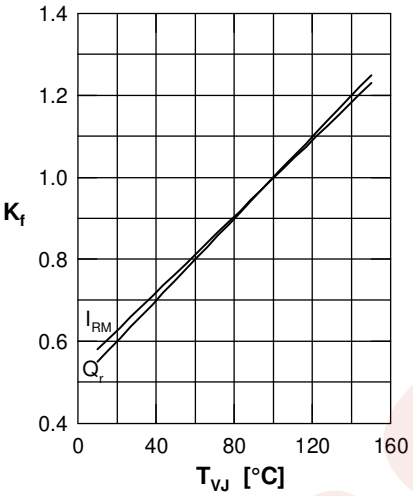


Fig. 4 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

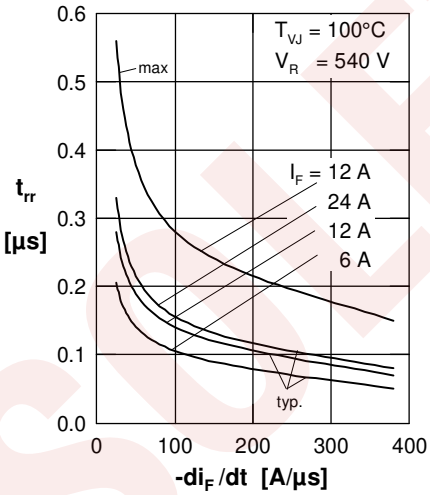


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

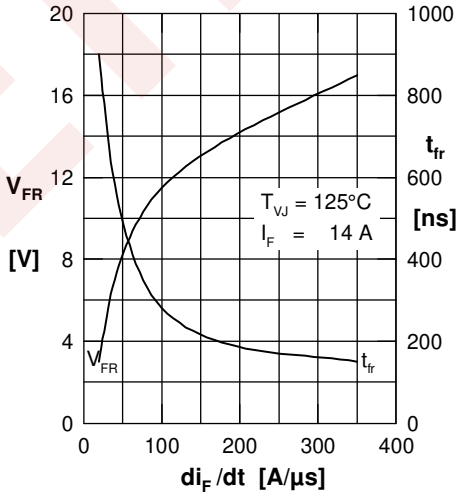


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

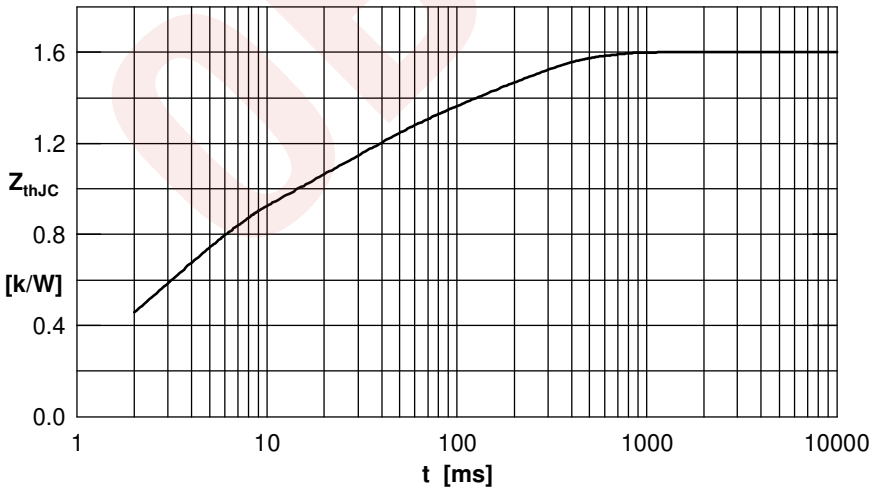


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.400	0.180
4	0.400	0.024
5	0.680	0.003

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